

Invited Speaker

Electron, spin and thermal transport at the nanoscale in molecular devices: a journey through recent results.

Dominique Vuillaume

*Institut d'Electronique Microelectronique et Nanotechnologie (IEMN), CNRS, Villeneuve d'Ascq, France.
dominique.vuillaume@iemn.fr*

I will review recent results on electron, spin and thermal transport at the nanoscale in molecular self-assembled monolayers (SAMs) and ultra-thin films. These results were mainly obtained by conductive-AFM (in air or UHV) and SThM (scanning thermal microscope) experiments and supported by ab-initio calculations. I will review and discuss:

- the transport properties of polyoxometalates (POMs), which are nano-scaled molecular oxides endowed with a remarkable structural diversity and outstanding magnetic and/or redox properties [1-3].
- the properties of Prussian blue analogs (PBAs) and related cyanide bridged systems, which are coordination networks with unique optical, magnetic, conducting and electrochemical properties [4].
- molecular switches (triggered by light or chemical stimuli) self-assembled on metal and ferromagnetic electrodes with the purpose, in the later case, to develop multifunctional molecular spintronics devices [5-8].
- the thermoelectric properties of organic films and SAMs to assess the role of molecular structures, molecule/electrode interfaces and quantum interferences [9-11].

[1] *Molecular signature of polyoxometalates in electron transport of silicon-based molecular junctions.*

Laurans, M.; Dalla Francesca, K.; Volatron, F.; Izzet, G.; Guerin, D.; Vuillaume, D.; Lenfant, S.; Proust, **Nanoscale** 2018, 10, 17156-17165.

[2] *Charge transport through redox active $[H_7P_8W_{48}O_{184}]^{33-}$ polyoxometalates self-assembled onto gold surfaces and gold nanodots.* Dalla Francesca, K.; Lenfant, S.; Laurans, M.; Volatron, F.; Izzet, G.; Humblot, V.; Methivier, C.; Guerin, D.; Proust, A.; Vuillaume, D. **Nanoscale** 2019, 11, 1863-1878..

[3] *Covalent Grafting of Polyoxometalate Hybrids onto Flat Silicon/Silicon Oxide: Insights from POMs Layers on Oxides.* Laurans, M.; Trinh, K.; Dalla Francesca, K.; Izzet, G.; Alves, S.; Derat, E.; Humblot, V.; Pluchery, O.; Vuillaume, D.; Lenfant, S.; Volatron, F. Proust, A. **ACS Appl. Mater. Interfaces** 2020, 12, 48109-48123.

[4] *Long-range electron transport in Prussian blue analog nanocrystals.* Bonnet, R.; Lenfant, S.; Mazerat, S.; Mallah, T.; Vuillaume, D. **Nanoscale** 2020, 12, 20374-20385.

[5] *Conductance switching at the nanoscale of diarylethene derivative self-assembled monolayers on $La_{0.7}Sr_{0.3}MnO_3$.* Thomas, L.; Guerin, D.; Quinard, B.; Jacquet, E.; Mattana, R.; Seneor, P.; Vuillaume, D.; Mélin, T.; Lenfant, S. **Nanoscale** 2020, 12, 8268-8276.

[6] *Conductance switching of azobenzene-based self-assembled monolayers on cobalt probed by UHV conductive-AFM.* Thomas, L.; Arbouch, I.; Guerin, D.; Wallart, X.; Van Dyck, C.; Melin, T.; Cornil, J.; Vuillaume, D.; Lenfant, S. **Nanoscale** 2021, 13, 6977-6990.

[7] *Diarylethene self-assembled monolayers on cobalt with high conductance switching ratio for spintronics.*

V. Prudkovskiy, I. Arbouch, Y. Pei, C. van Dyck, D. Guérin, S. Lenfant, T. Mallah, J. Cornil, D. Vuillaume, in preparation.

[8] *Electrical Molecular Switch Addressed by Chemical Stimuli.* Audi, H.; Viero, Y.; Alwhaibi, N.; Chen, Z.; lazykov, M.; Heynderickx, A.; Xiao, F.; Guerin, D.; Krzeminski, C.; Grace, I. M.; Lambert, C.J.; Siri, O., Vuillaume, D.; Lenfant, S.; Klein, H. **Nanoscale** 2020, 22, 10127-10139.

[9] *Thermal conductivity of benzothieno- benzothiophene derivatives at the nanoscale.* Gueye, M.; Vercouter, A.; Jouclas, R.; Guerin, D.; Lemaure, V.; Schweicher, G.; Lenfant, S.; Antidormi, A.; Geerts, Y.; Melis, C.; Cornil, J.; Vuillaume, D. **Nanoscale** 2021, 13, 3800-3807.

[10] *Correlation between nanoscale thermal and electrical conductivity in PEDOT:OTf thin films.* K. Kondratenko, D. Guérin, D. Deresmes, A. Carella, S. Lenfant and D. Vuillaume, in preparation.

[11] *Exploring thermoelectric properties of organometallic molecular junctions.* V. Delmas, S. Rigaut, V. Diaz-Cabanes, C. van Dyck, D. Vuillaume, E. Scheer, J. Cornil, and K. Costuas, in preparation.